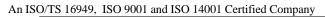
# Continental Device India Limited







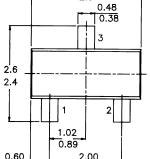
## **SOT-23 Formed SMD Package**

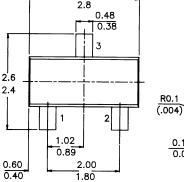
CSA1362

# LOW FREQUENCY POWER AMPLIFIER TRANSISTOR

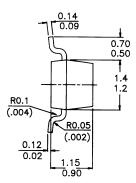
P-N-P transistor

Marking CSA1362GR = 62 PACKAGE OUTLINE DETAILS ALL DIMENSIONS IN mm





3.0



# Pin configuration

1 = BASE

2 = EMITTER 3 = COLLECTOR



#### ABSOLUTE MAXIMUM RATINGS

Collector-base voltage (open emitter)	$-V_{CBO}$	max.	15	V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	15	V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	5	V
Collector current (d.c.)	$-I_C$	max.	800	mA
Total power dissipation at $T_{amb} = 25^{\circ}C$	$P_{tot}$	max	200	mW
Junction temperature	$T_{j}$	max.	<i>150</i>	$^{\circ}$ $C$
D.C. current gain	,			
$-I_C = 100 \text{ mA; } -V_{CE} = 1 \text{ V}$	$h_{\!F\!E}$	min.	120	
		max	400	

#### **RATINGS** (at $T_A = 25^{\circ}C$ unless otherwise specified)

Limiting values

Collector-base voltage (open emitter)	$-V_{CBO}$	max.	15	V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	15	V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	5	V
Collector current (d.c.)	$-I_C$	max.	800	mA
Total power dissipation at $T_{amb} = 25$ °C	$P_{tot}$	max	<i>200</i>	mW

Storage temperature Junction temperature	T <sub>stg</sub> Tj	–55 max.	to +150 150	° C ° C
•	1)	тах.	100	C
THERMAL CHARACTERISTICS $T_{j} = P (R_{th j-t} + R_{th s-a}) + T_{amb}$ Thermal resistance				
from junction to ambient	$R_{th\ j-a}$		556	°C/mW
<b>CHARACTERISTICS</b> (at $T_A = 25^{\circ}C$ unless otherwise	se specified)			
Collector-emitter breakdown voltage $-I_C = 10 \text{ mA}$	-V <sub>(BR)</sub> CEC	) min.	15	V
Collector cut-off current				
$-V_{CB} = 15 V$	$-I_{CBO}$	max.	100	nA
Emitter cut-off current $V_{EB} = 5 V$	$I_{EBO}$	max.	100	nΑ
Saturation voltages $-I_C = 400 \text{ mA}; -I_B = 8 \text{ mA}$	-V <sub>CEsat</sub>	max.	0.25	V
Base Emitter on voltage				
$I_C = 10 \text{ mA}, \ V_{CE} = 1 \text{ V}$	-V <sub>BE(on)</sub>	min.	0.5	V
		max.	0.8	V
D.C. current gain				
$I_C = 100 \text{ mA; } -V_{CE} = 1 \text{ V}$	$h_{FE}$	min. max.	120 400	
	Y	min.	120	
		max.	240	
	GR	min. max.	200 400	
		шах.	400	
$I_C = 800 \text{ mA}; V_{CE} = 1 \text{ V}$		min.	40	
Transition frequency				
$V_{CE} = 5V, I_C = 10 \text{ mA}$	$f_T$	typ.	120	MHz
Collector output capacitance				
$V_{CB} = 10V, I_E = 0, f = 1 MHz$	$C_{ob}$	typ.	13	pF

## **Notes**

## **Disclaimer**

The product information and the selection guides facilitate selection of the CDIL's Discrete Semiconductor Device(s) best suited for application in your product(s) as per your requirement. It is recommended that you completely review our Data Sheet(s) so as to confirm that the Device(s) meet functionality parameters for your application. The information furnished on the CDIL Web Site/CD is believed to be accurate and reliable. CDIL however, does not assume responsibility for inaccuracies or incomplete information. Furthermore, CDIL does not assume liability whatsoever, arising out of the application or use of any CDIL product; neither does it convey any license under its patent rights nor rights of others. These products are not designed for use in life saving/support appliances or systems. CDIL customers selling these products (either as individual Discrete Semiconductor Devices or incorporated in their end products), in any life saving/support appliances or systems or applications do so at their own risk and CDIL will not be responsible for any damages resulting from such sale(s).

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